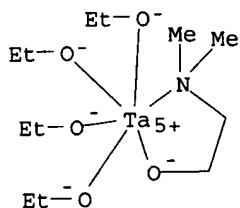


L7 ANSWER 1 OF 18 HCAPLUS COPYRIGHT 2003 ACS on STN  
 AN 2003:297795 HCAPLUS  
 DN 138:279838  
 TI Manufacturing method for dielectric layer of **capacitor**  
 IN Huang, Guo-Tai; You, Tsuei-Rung  
 PA United Microelectronics Corp., Taiwan  
 SO Taiwan, 17 pp.  
 CODEN: TWXXA5

DT Patent  
 LA Chinese  
 IC ICM H01L021-8242  
 ICS H01L021-76  
 CC 76-10 (Electric Phenomena)  
 FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	TW 410441	B	20001101	TW 1999-88110830	19990628
PRAI	TW 1999-88110830		19990628		
AB	Organometallic <b>precursor</b> for depositing Ta oxide dielec. layer on elec. <b>capacitor</b> is described. The single phase Ta oxide dielec. layers are formed by MOCVD. The dielec. const. of the dielec. layer can be adjusted by adjusting the compn. of the <b>precursor</b> . The process is used for the fabrication of DRAM memories.				
IT	1314-61-0P, Tantalum oxide Ta2O5 RL: DEV (Device component use); PNU (Preparation, unclassified); PRP (Properties); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses) (MOCVD with organometallic <b>precursor</b> for dielec. layer of <b>capacitor</b> for DRAM device fabrication)				
IT	6074-84-6, Tantalum pentaethoxide 169896-41-7 172901-22-3 177580-52-8 177580-53-9 238757-13-6 RL: RCT (Reactant); RACT (Reactant or reagent) (MOCVD with organometallic <b>precursor</b> for dielec. layer of <b>capacitor</b> for DRAM device fabrication)				
IT	172901-22-3 177580-52-8 177580-53-9 238757-13-6 RL: RCT (Reactant); RACT (Reactant or reagent) (MOCVD with organometallic <b>precursor</b> for dielec. layer of <b>capacitor</b> for DRAM device fabrication)				
RN	172901-22-3 HCAPLUS				
CN	Tantalum, [2-(dimethylamino-.kappa.N)ethanolato-.kappa.O]tetraethoxy-, (OC-6-23)- (9CI) (CA INDEX NAME)				



RN 177580-52-8 HCAPLUS  
 CN Tantalum, tetraethoxy(2,2,6,6-tetramethyl-3,5-heptanedionato-.kappa.O,.kappa.O')-, (OC-6-22)- (9CI) (CA INDEX NAME)